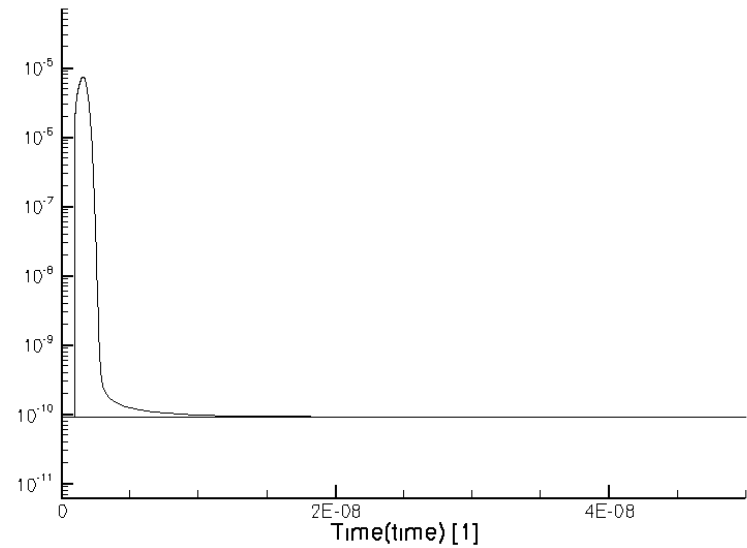
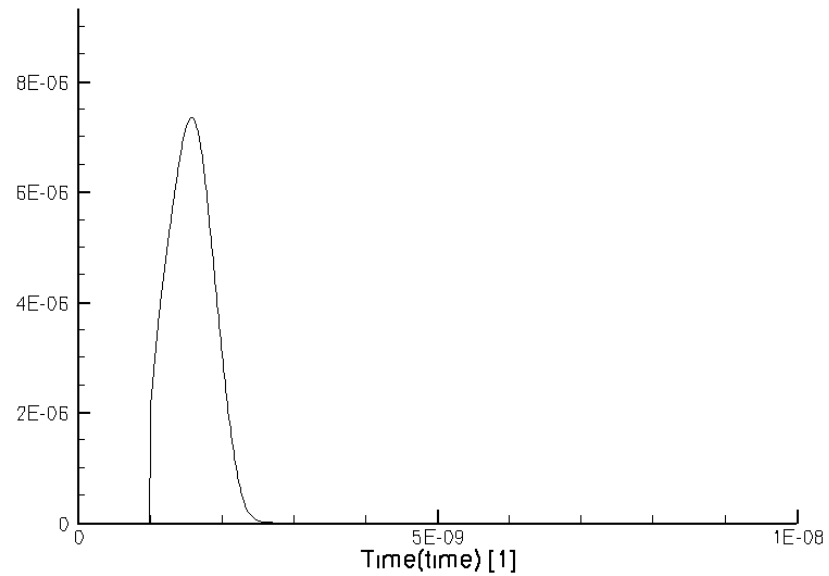


Sensor simulation

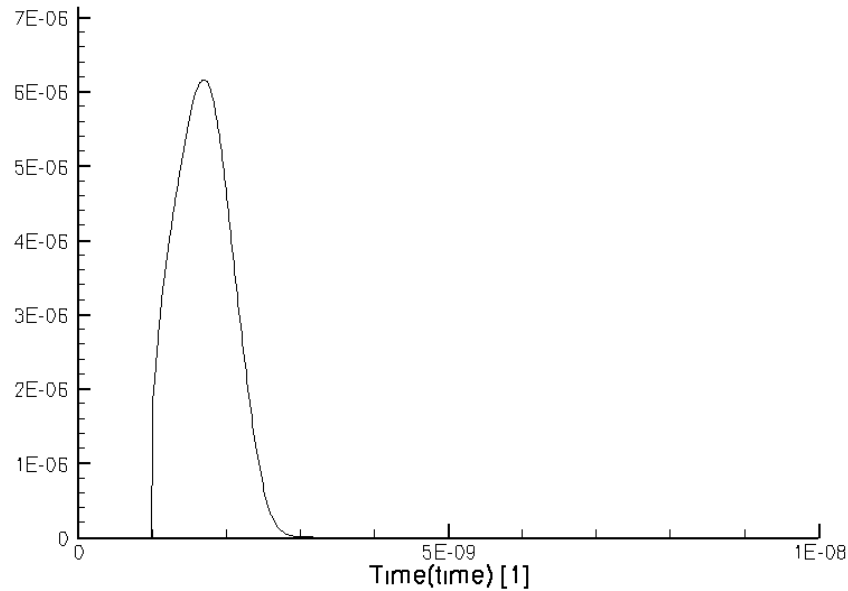
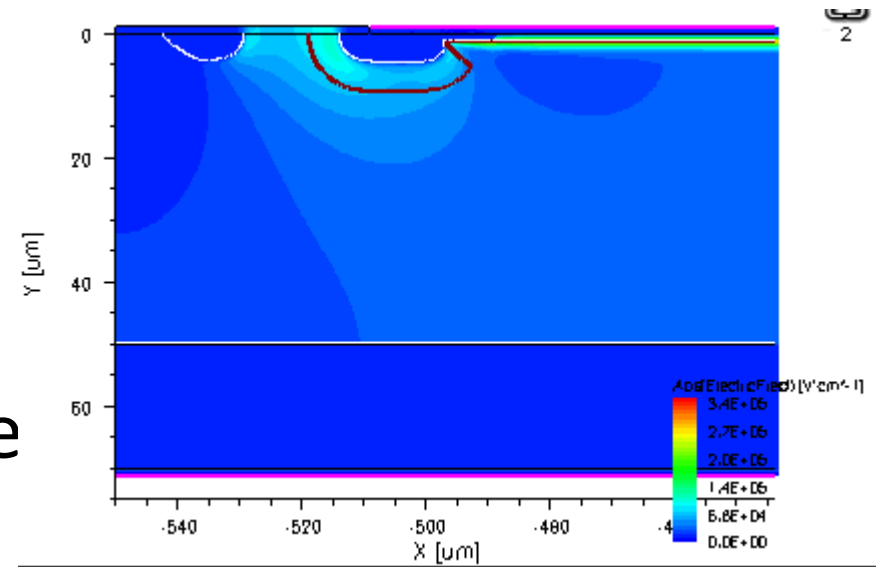
Mei Zhao

2018.12.6

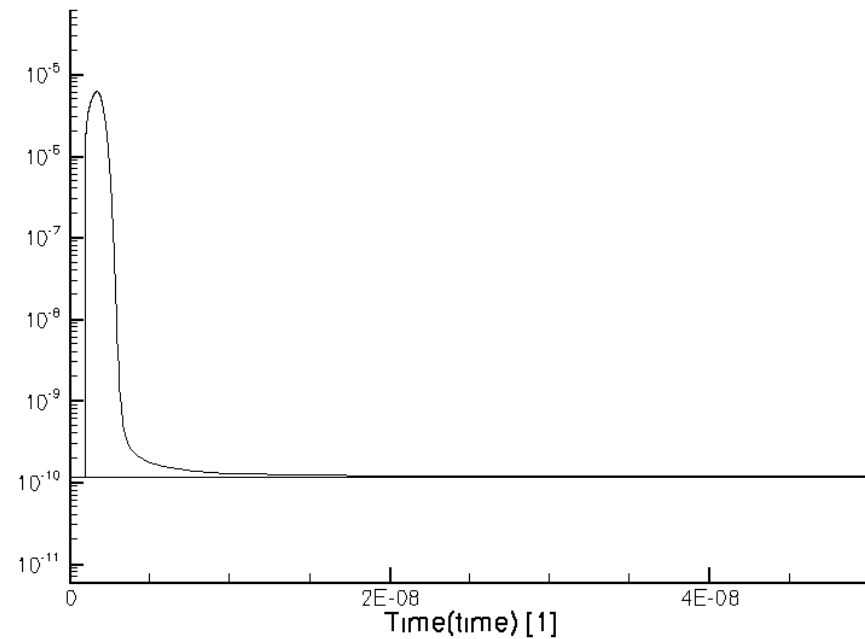
- One model
- Break down at 350V
- Gain~10 at 300V



- Another model
- Change doping profile
- Gain ~ 10 at 150V

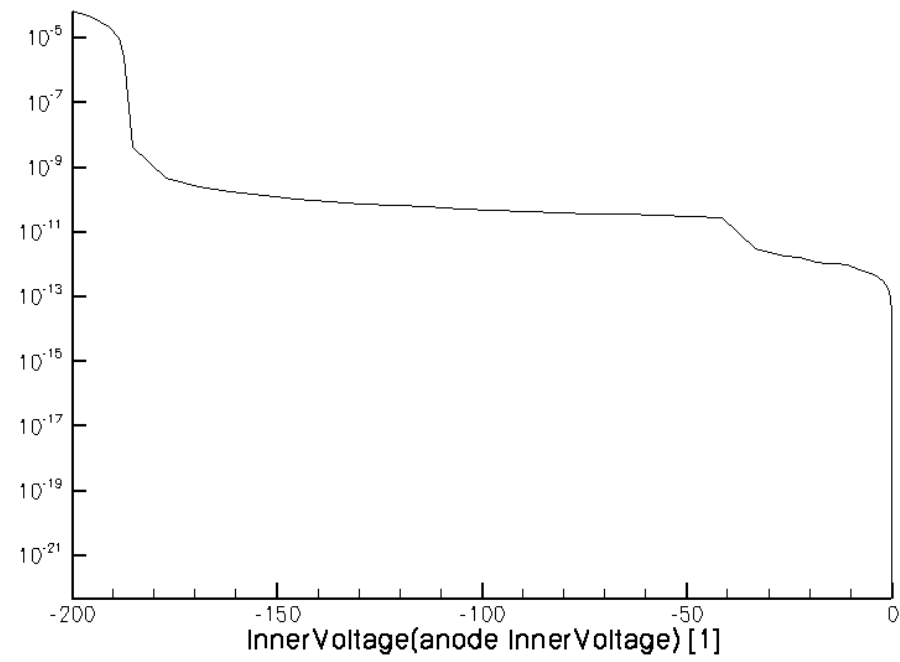


Signal at 150V(A/um)



Leakage current at 150V (A/um)

- I-V curve



- Get a suitable gain at lower voltage(150V)
- Discuss the process of the sensor fabrication with Thinghua
- Next draw layout